

CMPT5551E

**ENHANCED SPECIFICATION  
SURFACE MOUNT  
NPN SILICON TRANSISTOR**



www.centrasemi.com



SOT-23 CASE

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CMPT5551E is an NPN Silicon Transistor, packaged in an SOT-23 case, designed for general purpose amplifier applications requiring high breakdown voltage and small space saving packaging.

**MARKING CODE: C555**

**FEATURES:**

- High Collector Breakdown Voltage 250V
- Low Leakage Current 50nA Max
- Low Saturation Voltage 100mV Max @ 50mA
- Complementary Device CMPT5401E
- SOT-23 Surface Mount Package

**APPLICATIONS:**

- General purpose switching and amplification
- Telephone applications

**MAXIMUM RATINGS:** ( $T_A=25^\circ\text{C}$ )

◆ Collector-Base Voltage	
◆ Collector-Emitter Voltage	
Emitter-Base Voltage	
Continuous Collector Current	
Power Dissipation	
Operating and Storage Junction Temperature	
Thermal Resistance	

SYMBOL		UNITS
$V_{CBO}$	250	V
$V_{CEO}$	220	V
$V_{EBO}$	6.0	V
$I_C$	600	mA
$P_D$	350	mW
$T_J, T_{stg}$	-65 to +150	$^\circ\text{C}$
$\theta_{JA}$	357	$^\circ\text{C/W}$

**ELECTRICAL CHARACTERISTICS:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
$I_{CBO}$	$V_{CB}=120\text{V}$		50	nA
$I_{CBO}$	$V_{CB}=120\text{V}, T_A=100^\circ\text{C}$		50	$\mu\text{A}$
$I_{EBO}$	$V_{EB}=4.0\text{V}$		50	nA
◆ $BV_{CBO}$	$I_C=100\mu\text{A}$	250		V
◆ $BV_{CEO}$	$I_C=1.0\text{mA}$	220		V
$BV_{EBO}$	$I_E=10\mu\text{A}$	6.0		V
◆ $V_{CE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$		75	mV
◆ $V_{CE(SAT)}$	$I_C=50\text{mA}, I_B=5.0\text{mA}$		100	mV
$V_{BE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$		1.00	V
$V_{BE(SAT)}$	$I_C=50\text{mA}, I_B=5.0\text{mA}$		1.00	V
◆ $h_{FE}$	$V_{CE}=5.0\text{V}, I_C=1.0\text{mA}$	120		
◆ $h_{FE}$	$V_{CE}=5.0\text{V}, I_C=10\text{mA}$	120	300	
◆ $h_{FE}$	$V_{CE}=5.0\text{V}, I_C=50\text{mA}$	75		
◆ $h_{FE}$	$V_{CE}=10\text{V}, I_C=150\text{mA}$	25		
$f_T$	$V_{CE}=10\text{V}, I_C=10\text{mA}, f=100\text{MHz}$	100	300	MHz

◆ Enhanced specification

R1 (1-February 2010)

CMPT5551E

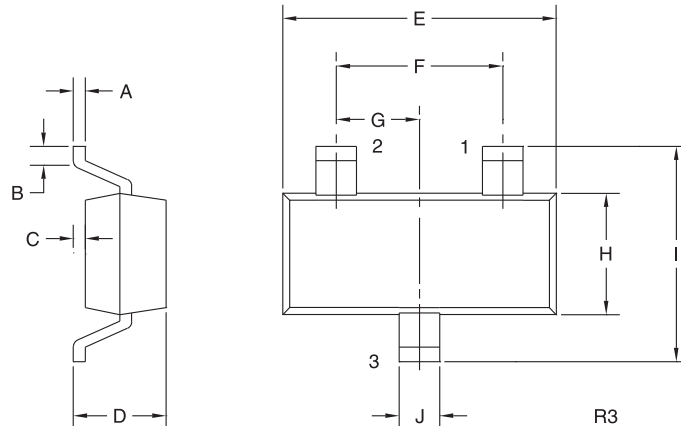
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**ELECTRICAL CHARACTERISTICS - Continued:** ( $T_A=25^{\circ}\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
$C_{ob}$	$V_{CB}=10\text{V}$ , $I_E=0$ , $f=1.0\text{MHz}$		6.0	pF
$C_{ib}$	$V_{EB}=0.5\text{V}$ , $I_C=0$ , $f=1.0\text{MHz}$		20	pF
$h_{fe}$	$V_{CE}=10\text{V}$ , $I_C=1.0\text{mA}$ , $f=1.0\text{kHz}$	50	200	
NF	$V_{CE}=5.0\text{V}$ , $I_C=200\mu\text{A}$ , $R_S=10\Omega$ , $f=10\text{Hz}$ to $15.7\text{kHz}$		8.0	dB

**SOT-23 CASE - MECHANICAL OUTLINE**



**LEAD CODE:**

- 1) Base
- 2) Emitter
- 3) Collector

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SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.003	0.007	0.08	0.18
B	0.006	-	0.15	-
C	-	0.005	-	0.13
D	0.035	0.043	0.89	1.09
E	0.110	0.120	2.80	3.05
F	0.075		1.90	
G	0.037		0.95	
H	0.047	0.055	1.19	1.40
I	0.083	0.098	2.10	2.49
J	0.014	0.020	0.35	0.50

SOT-23 (REV: R3)

R1 (1-February 2010)